

26. (Amended) The method of fabricating a thin film transistor according to claim 25, wherein the substrate includes [one of a glass and an oxide layer on a glass] a material selected from the group consisting of a glass and a glass having an oxide layer formed thereon.

27. (Amended) The method of fabricating a thin film transistor according to claim 25, wherein the substrate [is prepared by depositing a silicon wafer or an oxide layer on a silicon wafer] includes a material selected from the group consisting of a silicon wafer and a silicon wafer having an oxide layer formed thereon.

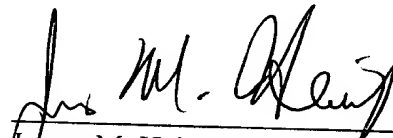
REMARKS

In view of the foregoing amendment, all claims are believed to be in condition for immediate allowance. Allowance of the application is respectfully solicited.

Respectfully submitted,

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